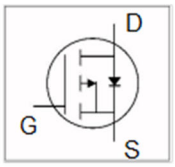
KGEY 金易半 Kingeavysemi

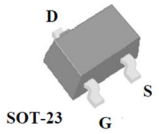
# KE2300T0U-L

*N-CHANNEL ENHANCEMENT MODE POWER MOSFET*

- **Simple Drive Requirement**
- **Small Package Outline**
- **Surface Mount Device**
- **RoHS Compliant & Halogen-Free**




| | |
|---|---|
| BVDSS | 20V |
| RDS(ON)typ | 21mΩ |
| ID | 5A |




## Description

KE2300 is from Kingeavy innovated design and silicon process technology to achieve the lowest possible on- resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

## Absolute Maximum Ratings@$T_J$=25°C(unless otherwise specified)

| Symbol | Parameter | Rating | Units |
|---|---|---|---|
| $V_{DS}$ | Drain-Source Voltage | 20 | V |
| $V_{GS}$ | Gate-Source Voltage | ±8 | V |
| $I_D$@$T_A$=25℃ | Drain Current, $V_{GS}$ @ 10V | 5 | A |
| $I_D$@$T_A$=70℃ | Drain Current, $V_{GS}$ @ 10V | 4 | A |
| $I_{DM}$ | Pulsed Drain Current2 | 20 | A |
| $P_D$@$T_A$=25℃ | Total Power Dissipation3 | 0.6 | W |
| $T_{STG}$ | Storage Temperature Range | -55 to 150 | ℃ |
| $T_J$ | Operating Junction Temperature Range | 150 | ℃ |

## Thermal Data

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| Rthj-a | Maximum Thermal Resistance, Junction-ambient3 | 150 | ℃/W |

## Electrical Characteristics@$T_j$=25 oC(unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | VGS=0V, ID=250uA | 20 | - | - | V |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | VGS=4.5V, ID=5A | - | 21 | 28 | mΩ |
| | | VGS=2.5V, ID=4A | - | 26 | 37 | mΩ |
| | | VGS=1.8V, ID=3A | - | 38 | 75 | mΩ |
| $V_{GS(th)}$ | Gate Threshold Voltage | VDS=VGS, ID=250uA | 0.5 | 0.65 | 1.2 | V |
| $g_{fs}$ | Forward Transconductance | VDS=5V, ID=5A | 6 | - | - | S |
| $I_{DSS}$ | Drain-Source Leakage Current | VDS=19V, VGS=0V | - | - | 1 | uA |
| $I_{GSS}$ | Gate-Source Leakage | VGS=±12V, VDS=0V | - | - | ±100 | nA |
| $Q_g$ | Total Gate Charge | ID=2A<br>VDS=10V<br>VGS=4.5V | - | 3.4 | - | nC |
| $Q_{gs}$ | Gate-Source Charge | | - | 0.6 | - | nC |
| $Q_{gd}$ | Gate-Drain ("Miller") Charge | | - | 1.6 | - | nC |
| $t_{d(on)}$ | Turn-on Delay Time | VDS=10V<br>ID=2A<br>RG=1Ω<br>VGS=4.5V,RL=2.2Ω | - | - | 10 | ns |
| $t_r$ | Rise Time | | - | - | 20 | ns |
| $t_{d(off)}$ | Turn-off Delay Time | | - | - | 32 | ns |
| $t_f$ | Fall Time | | - | - | 12 | ns |
| $C_{iss}$ | Input Capacitance | VGS=0V<br>VDS=10V<br>f=1.0MHz | - | 270 | - | pF |
| $C_{oss}$ | Output Capacitance | | - | 35 | - | pF |
| Crss | Reverse Transfer Capacitance | | - | 25 | - | pF |

## Source-Drain Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| $V_{SD}$ | Forward On Voltage² | IS=2A, VGS=0V | - | 0.75 | 1.2 | V |

**Notes:**

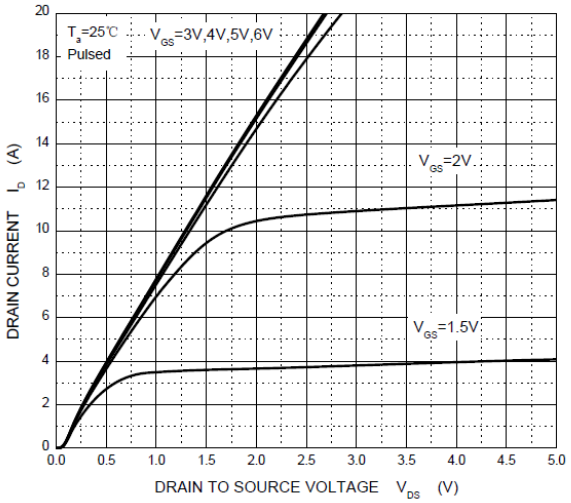
1.Pulse width limited by Max. junction temperature.

2.Pulse test

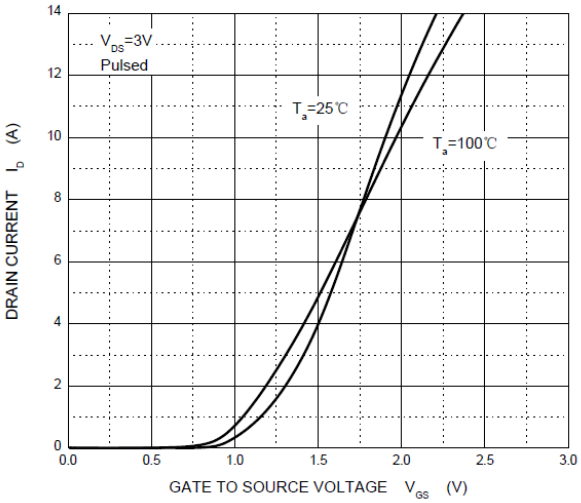
3.Surface mounted on 1 $in^2$ 2oz copper pad of FR4 board, t ≤10sec ; 300°C/W when mounted on min. copper pad.

## Typical Performance Characteristics

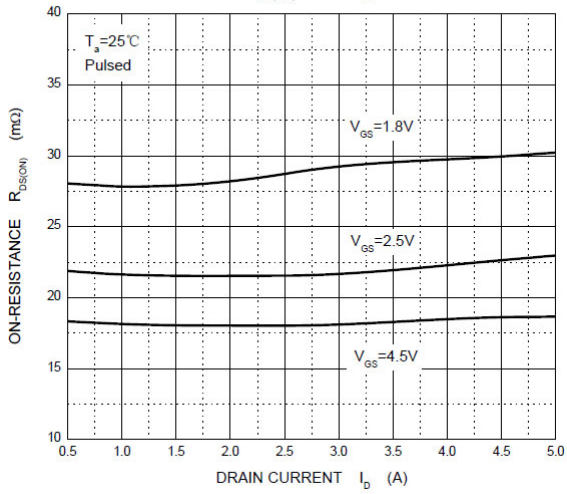
Output Characteristics



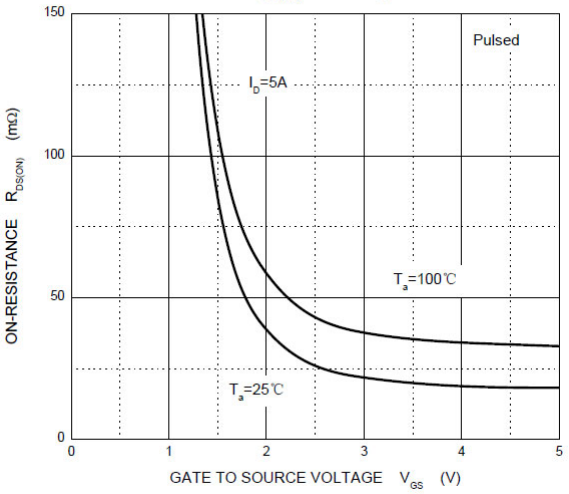

Transfer Characteristics



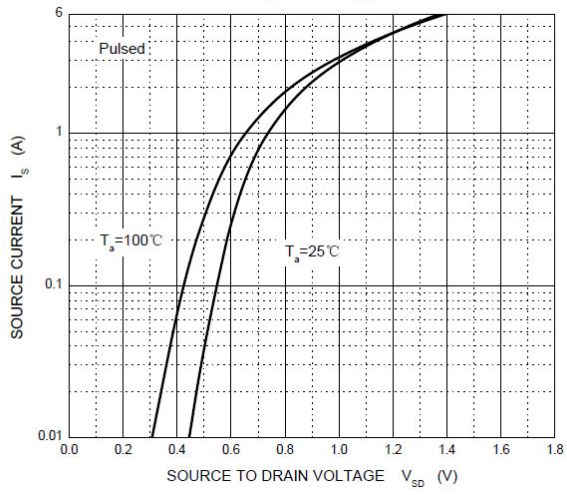

$R_{DS(ON)}$ —— $I_D$



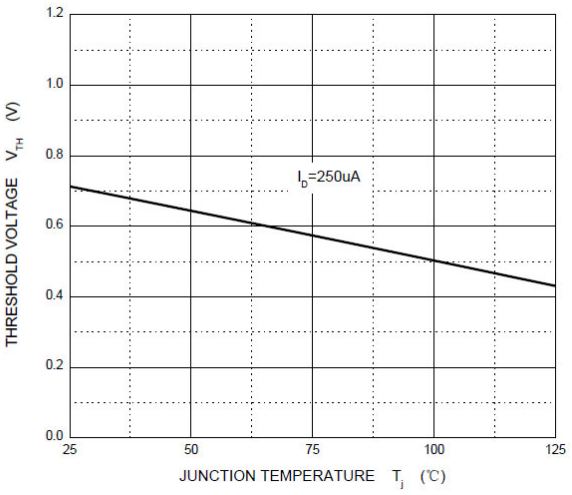

$R_{DS(ON)}$ —— $V_{GS}$



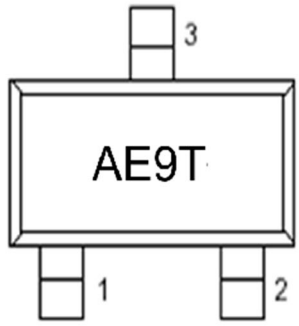

$I_S$ —— $V_{SD}$



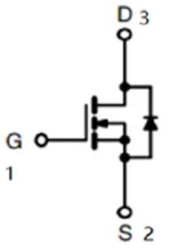

Threshold Voltage



## Marking Information

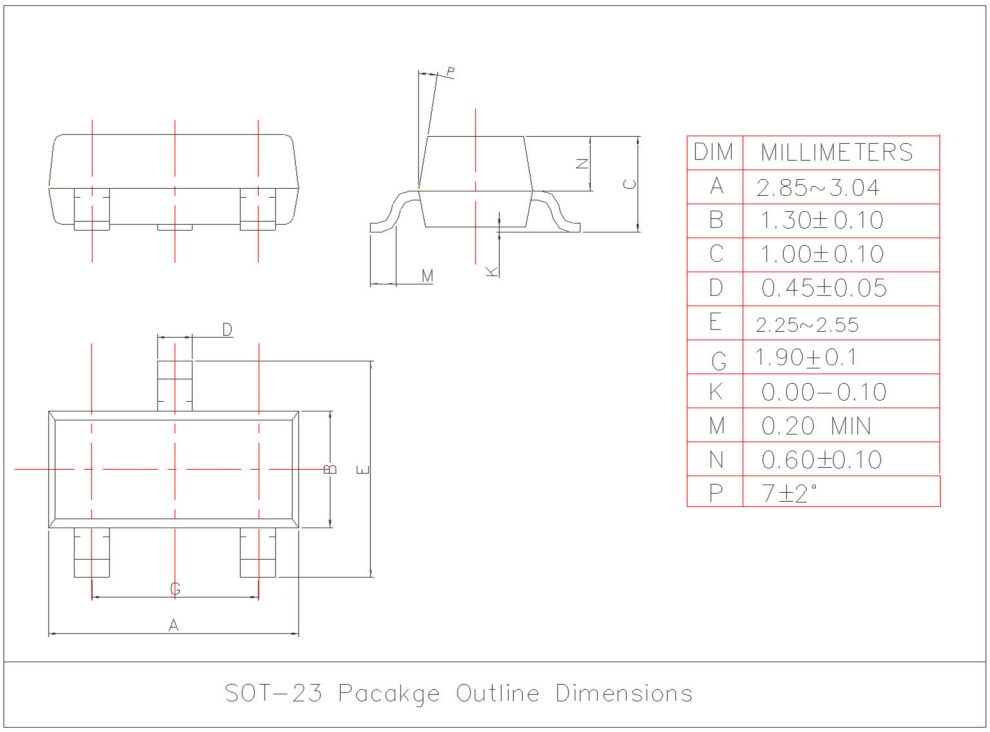



Top view




印字 **marking：AE9T**

## Package Outline : SOT-23




| DIM | MILLIMETERS |
|---|---|
| A | 2.85~3.04 |
| B | 1.30±0.10 |
| C | 1.00±0.10 |
| D | 0.45±0.05 |
| E | 2.25~2.55 |
| G | 1.90±0.1 |
| K | 0.00−0.10 |
| M | 0.20 MIN |
| N | 0.60±0.10 |
| P | 7±2° |

SOT−23 Pacakge Outline Dimensions